

a common drain wiring connected with said at least two transistors at the other of the source and drain of each of said at least two transistors,

wherein said at least two transistors are connected with each other in parallel by the connections of said common gate wiring, said common source wiring, and said common drain wiring with said at least two transistors, and

wherein channel-forming regions of said at least two transistors are separately provided in at least two separate semiconductor layers respectively.

2. (Thrice Amended) An active matrix type display device comprising:

a plurality of pixels arranged in matrix form over a substrate;

a driver circuit for driving the plurality of pixels over said substrate;

at least two transistors in said driver circuit;

a common gate wiring connected with said at least two transistors at gate electrodes of said at least two transistors;

a common source wiring connected with said at least two transistors at one of source and drain of each of said at least two transistors;

a common drain wiring connected with said at least two transistors at the other of the source and drain of each of said at least two transistors,

wherein said at least two transistors are connected with each other in parallel by the connections of said common gate wiring, said common source wiring, and said common drain wiring with said at least two transistors, and

wherein channel-forming regions of said at least two transistors are separately provided in at least two separate semiconductor layers respectively.

3. (Thrice Amended) An active matrix type display device comprising:

a plurality of pixels arranged in matrix form over a substrate;

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a driver circuit for driving the plurality of pixels over said substrate, said driver circuit including at least one buffer circuit;

at least two transistors in said at least one buffer circuit;

a common gate wiring connected with said at least two transistors at gate electrodes of said at least two transistors;

a common source wiring connected with said at least two transistors at one of source and drain of each of said at least two transistors;

a common drain wiring connected with said at least two transistors at the other of the source and drain of each of said at least two transistors,

wherein said at least two transistors are connected with each other in parallel by the connections of said common gate wiring, said common source wiring, and said common drain wiring with said at least two transistors, and

wherein channel-forming regions of said at least two transistors are separately provided in at least two separate semiconductor layers respectively and each of said channel-forming regions not having linear defects or surface defects.

8. (Thrice Amended) An active matrix type display device comprising:

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a plurality of pixels arranged in matrix form over a substrate;

a driver circuit for driving the plurality of pixels over said substrate;

at least two transistors in said driver circuit in said active matrix type display device;

a common gate wiring connected with said at least two transistors at gate electrodes of said at least two transistors;

a common source wiring connected with said at least two transistors at one of source and drain of each of said at least two transistors;

H2 a common drain wiring connected with said at least two transistors at the other of the source and drain of each of said at least two transistors,

wherein said at least two transistors are connected with each other in parallel by the connections of said common gate wiring, said common source wiring and said common drain wiring with said at least two transistors, and

wherein channel-forming regions of said at least two transistors are separately provided in at least two separate semiconductor layers respectively and each of said channel-forming regions not having linear defects or surface defects.

Please add new claims 100-103 as follows.

H3 --100. (New) The device of claim 1, wherein each of said channel-forming regions contains carbon and nitrogen at a concentration of $5 \times 10^{18} \text{ cm}^{-3}$ or less, respectively, and contains oxygen at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

101. (New) The device of claim 2, wherein each of said channel-forming regions contains carbon and nitrogen at a concentration of $5 \times 10^{18} \text{ cm}^{-3}$ or less, respectively, and contains oxygen at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

102. (New) The device of claim 3, wherein each of said channel-forming regions contains carbon and nitrogen at a concentration of $5 \times 10^{18} \text{ cm}^{-3}$ or less, respectively, and contains oxygen at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

103. (New) The device of claim 8, wherein each of said channel-forming regions contains carbon and nitrogen at a concentration of $5 \times 10^{18} \text{ cm}^{-3}$ or less, respectively, and contains oxygen at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.--
